ABSTRACT OF THE DISCLOSURE

According to the present invention, in a boost voltage circuit, a plurality of N channel typed MOS transistors are connected between an input terminal and an output terminal in series and one electrode of each N channel typed MOS transistor to each of external terminals VC1 to VC5 to which a capacitor can be connected to generate a boost voltage. Each of P channel typed MOS transistors are connected to each in parallel in the boost voltage circuit with the above constitution. Thereby, it is possible to provide a boost voltage circuit to improve stability in staring the boost voltage circuit without increase of the consumption current.